

### AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-17 (canceled)

18. (Previously presented) A manufacturing method for an SOI wafer, comprising:

bonding an active layer wafer with a supporting wafer via an insulating film to form a bonded wafer body;

reducing a film thickness in a part of the active layer wafer that forms a part of the bonded wafer body to form an SOI layer for manufacturing the SOI wafer, wherein

the supporting wafer has a nitrogen concentration in a range of  $1 \times 10^{14}$  atoms/cm<sup>3</sup> to  $3 \times 10^{15}$  atoms/cm<sup>3</sup> and an oxygen concentration of equal to or higher than  $12 \times 10^{17}$  atoms/cm<sup>3</sup> when measured in accordance with old ASTM so as to have an oxidation induced stacking fault substantially entirely across a surface thereof.

19. (Cancelled)

20. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 18, further comprising:

ion-implanting one of hydrogen gas and a noble gas element to the active layer wafer to form an ion-implanted layer in the active layer wafer, prior to said bonding; and heat treating the bonded wafer body to induce cleavage in the bonded wafer body at the

site of the ion-implanted layer as an interface so as to form the SOI layer with a remaining active layer.

21. (Cancelled)

22. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 18, wherein a thickness of the SOI layer is thinner than  $0.10\mu\text{m}$ .

23. (Cancelled)

24. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 20, wherein a thickness of the SOI layer is thinner than  $0.10\mu\text{m}$ .

25. (Cancelled)

26. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 18 further comprising one of:

applying a rapid thermal process at a temperature in a range of  $1100\text{ }^{\circ}\text{C}$  to  $1250\text{ }^{\circ}\text{C}$  for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of  $1050\text{ }^{\circ}\text{C}$  to  $1250\text{ }^{\circ}\text{C}$  for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

27. (Cancelled)

28. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 20 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

29. (Cancelled)

30. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 22 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

31. (Cancelled)

32. (Previously presented) The manufacturing method of an SOI wafer in accordance with claim 24 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

33. (Cancelled)

34. (Previously presented) An SOI wafer manufactured by the following method:

bonding an active layer wafer with a supporting wafer via an insulating film to form a bonded wafer body;

reducing a film thickness in a part of the active layer wafer that forms a part of the bonded wafer body to form an SOI layer for manufacturing the SOI wafer, wherein

the supporting wafer has a nitrogen concentration in a range of  $1 \times 10^{14}$  atoms/cm<sup>3</sup> to  $3 \times 10^{15}$  atoms/cm<sup>3</sup> and an oxygen concentration of equal to or higher than  $12 \times 10^{17}$  atoms/cm<sup>3</sup> when measured in accordance with old ASTM so as to have an oxidation induced stacking fault entirely across a surface thereof; and a thickness of the SOI layer is thinner than 0.10 μm.

35. (Cancelled)